

AMENDMENTS TO THE SPECIFICATION:

Please amend paragraph [022] on page 7 to read as follows:

Referring to Fig. 2C, an etch back step with a second etchant is performed to remove the remaining tungsten silicide 36'. In one embodiment, the second etchant includes ~~an acid~~ a base such as $\text{NH}_4\text{OH}/\text{H}_2\text{O}_2$. The etch back process based on the second etchant is performed at a temperature ranging from approximately 55°C to 75°C. With respect to the second etchant, tungsten silicide is etched selectively relative to polycrystalline silicon. The etch-back step reduces sidewalls 36-2 of tungsten silicide layer 36.